

Technology & Industry Alliances Available Technologies Contact Us **Request Information** Permalink **Tunnel Junction Devices with Optically-Pumped III-Nitride Layers** CONTACT Pasquale S. Ferrari Tech ID: 27412 / UC Case 2016-324-0 ferrari@tia.ucsb.edu tel: . **BRIEF DESCRIPTION** A method of replacing standard electrical injection of the quantum wells in semiconductor devices with opticallypumping, by coupling a short-wavelength electrically pumped active region to a long-wavelength optically pumped **OTHER INFORMATION** region via a tunnel junction. **KEYWORDS** BACKGROUND Tunnel Junction, indled, III-Despite the inherent advantages of growing III-N semiconductor devices on nonpolar and semipolar planes, Nitride, Optically-pumped, challenges still remain for the emission of green, yellow, orange, and red light. High-indium content layers are LEDs, Laser Diodes, Light necessary for long emission wavelengths, but are difficult to achieve because the current growth process involves Emitting Diodes, Quantum high temperature steps that can degrade high-indium-content layers. Wells, indfeat DESCRIPTION **CATEGORIZED AS** Researchers at the University of California, Santa Barbara have developed a method of replacing standard electrical Optics and Photonics injection of the quantum wells in semiconductor devices with optically-pumping, by coupling a short-wavelength All Optics and electrically pumped active region to a long-wavelength optically pumped region via a tunnel junction. Optically Photonics pumping allows for the creation of multiple quantum wells, thereby reducing the relaxation of high-indium content Semiconductors Other layers. Epi stacks optimized for optical pumping may be grown at lower temperatures. Additionally, with optically pumping long wavelength quantum wells, the doping profile can be engineering to optimize the emission wavelength. **RELATED CASES** 2016-324-0

ADVANTAGES

- Easier than electrical injection for producing long wavelength emission
- Reduced relaxation of high-indium content layers
- Doping profile can be engineered to optimize the emission wavelength
- Easy incorporation of 2-D light-emitting structures

APPLICATIONS

- ► LEDs
- Laser diodes

PATENT STATUS

Country	Туре	Number	Dated	Case
United States Of America	Issued Patent	11,411,137	08/09/2022	2016-324

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